

# Polar™ Power MOSFET

## HiPerFET™

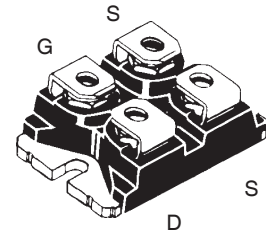
# IXFN30N110P

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$V_{DSS} = 1100V$   
 $I_{D25} = 25A$   
 $R_{DS(on)} \leq 360m\Omega$   
 $t_{rr} \leq 300ns$

miniBLOC, SOT-227 B (IXFN)  
 E153432



G = Gate      D = Drain  
 S = Source

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1100	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	25	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	75	A
$I_{AR}$	$T_C = 25^\circ C$	15	A
$E_{AS}$	$T_C = 25^\circ C$	1.5	J
<b>dV/dt</b>	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	695	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS	t = 1min	2500 V~
	$I_{ISOL} \leq 1mA$	t = 1s	3000 V~
$M_d$	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

### Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

### Advantages

- Easy to mount
- Space savings
- High power density

### Applications:

- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

Symbol	Test Conditions ( $T_J = 25^\circ C$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	1100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	3.5		6.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$			50 $\mu A$
	$V_{GS} = 0V$ $T_J = 125^\circ C$			2.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 15A$ , Note 1			360 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 15\text{A}$ , Note 1	15	25	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		13.6	nF
$C_{oss}$			795	pF
$C_{rss}$			70	pF
$R_{Gi}$	Gate input resistance		1.50	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 15\text{A}$ $R_G = 1\Omega$ (External)		50	ns
$t_r$			48	ns
$t_{d(off)}$			83	ns
$t_f$			52	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 15\text{A}$		235	nC
$Q_{gs}$			102	nC
$Q_{gd}$			79	nC
$R_{thJC}$			0.18	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			30 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			120 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 20\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			1.8	$\mu\text{C}$
$I_{RM}$			13	A

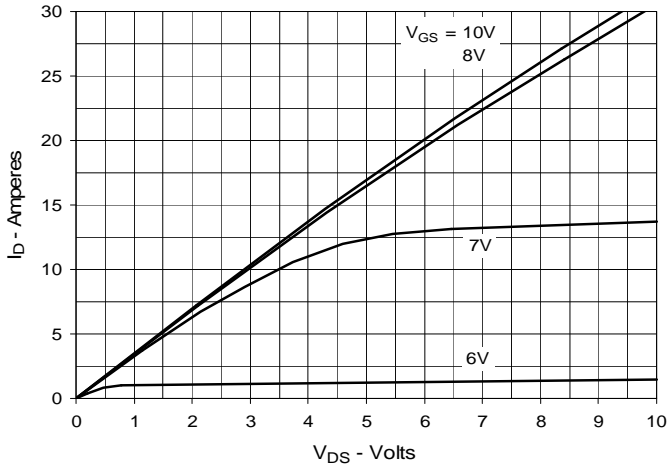
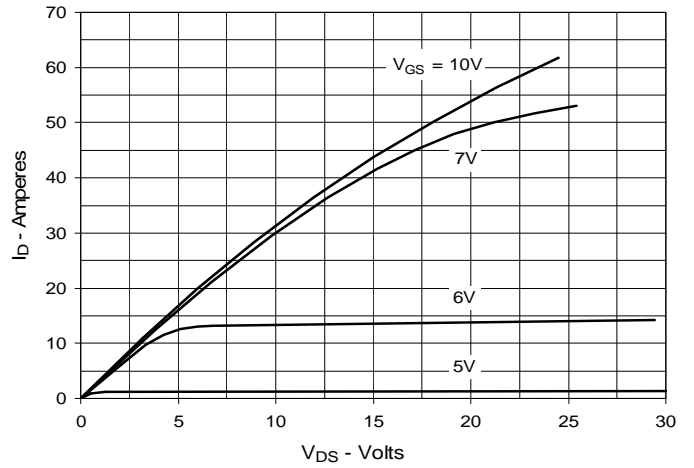
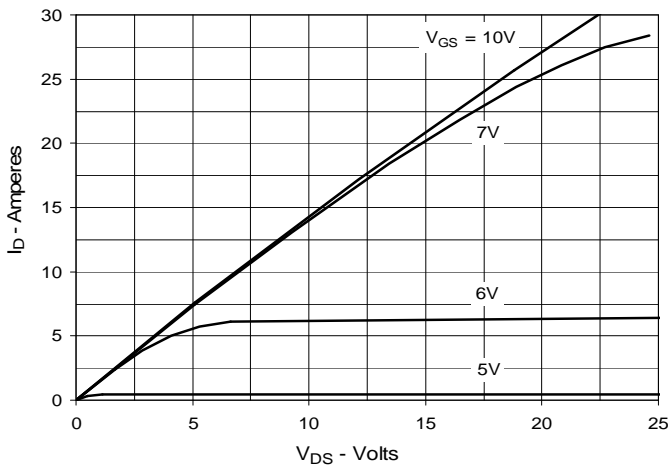
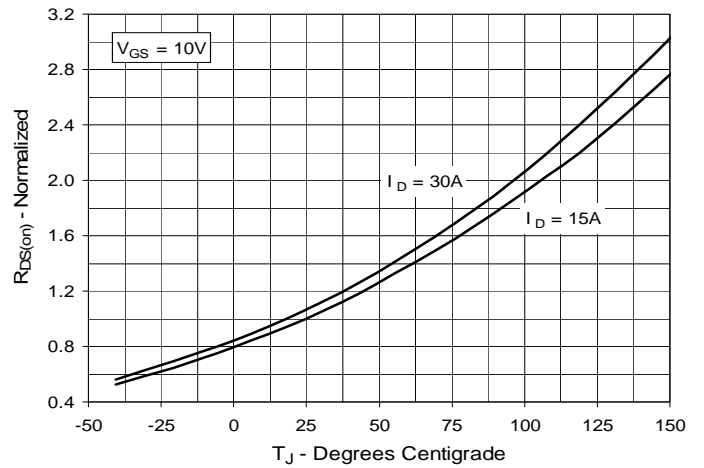
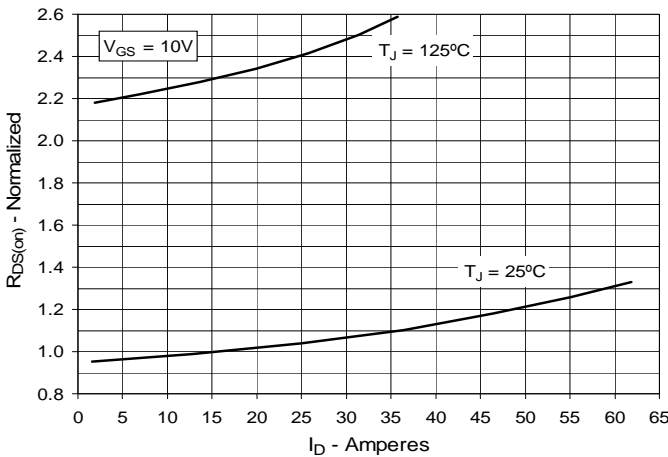
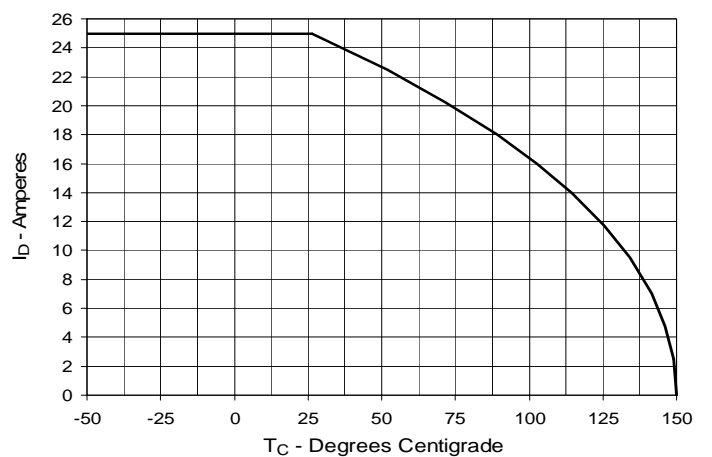
Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

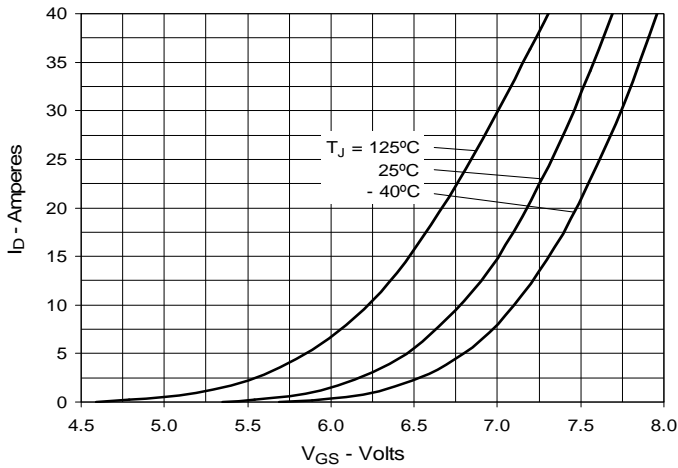
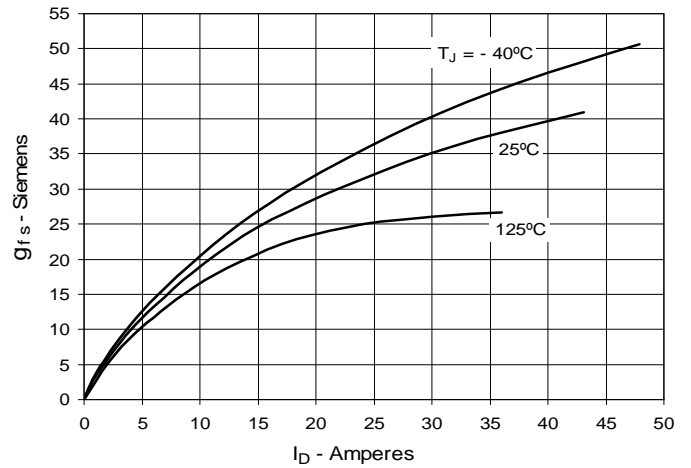
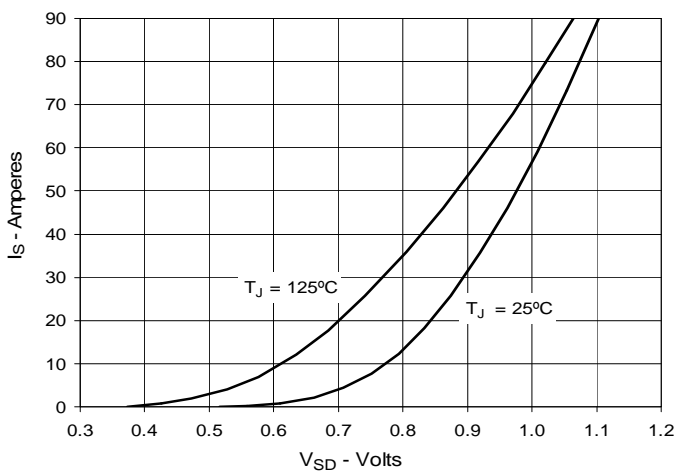
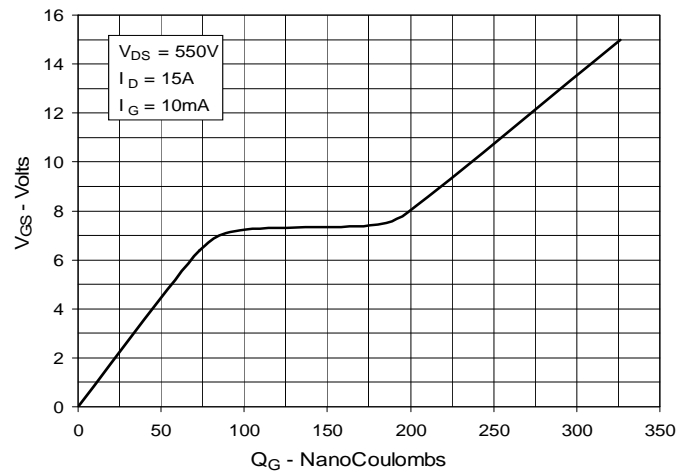
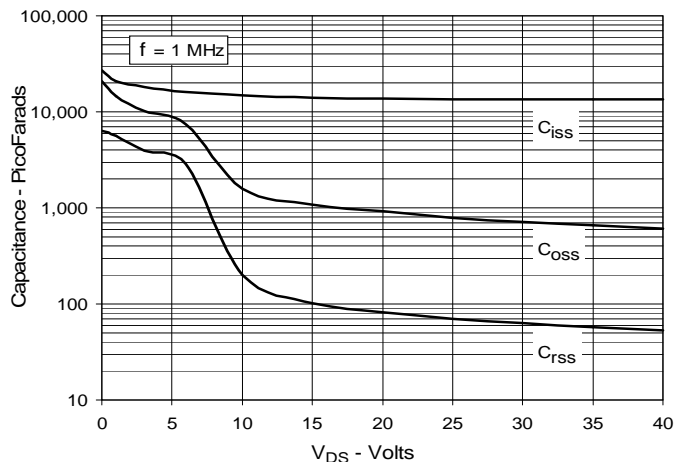
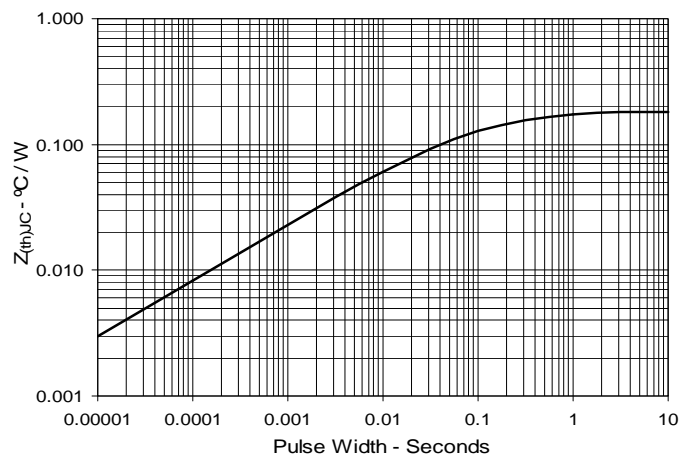
**SOT-227B Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @ 25°C**

**Fig. 2. Extended Output Characteristics @ 25°C**

**Fig. 3. Output Characteristics @ 125°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 15\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 15\text{A}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Maximum Transient Thermal Impedance**


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